

L Number	Hits	Search Text	DB	Time stamp
1	1610	(438/309,312,342,343,455).CCLS.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/01 09:20
2	263	((438/309,312,342,343,455).CCLS.) and (SiC or (silicon adj carbide) or (carburized adj silicon))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/01 09:26
3	206	((((438/309,312,342,343,455).CCLS.) and (SiC or (silicon adj carbide) or (carburized adj silicon))) and (@ad<20011121 or @rlad<20011121))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/01 09:37
4	19	(((((438/309,312,342,343,455).CCLS.) and (SiC or (silicon adj carbide) or (carburized adj silicon))) and (@ad<20011121 or @rlad<20011121)) and collector with (SiC or (silicon adj carbide) or (carburized adj silicon)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/01 09:37
5	19	(((((438/309,312,342,343,455).CCLS.) and (SiC or (silicon adj carbide) or (carburized adj silicon))) and (@ad<20011121 or @rlad<20011121)) and (collector with (SiC or (silicon adj carbide) or (carburized adj silicon))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/01 09:38
-	1097	(bjt or (bipolar adj transistor)) and ((silicon adj carbide) or SiC)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/07 10:06
-	28	((bjt or (bipolar adj transistor)) and ((silicon adj carbide) or SiC)) and (wafer adj (bond or bonded))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/10 14:23
-	133	(bjt or (bipolar adj transistor)) and (((silicon adj carbide) or SiC) with collector)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/10 17:43
-	2	("5144398" "5247192").PN.	USPAT	2003/09/10 17:08
-	2	5378901.URPN.	USPAT	2003/09/10 17:10
-	5	5272096.URPN.	USPAT	2003/09/10 17:22
-	3	("4945394" "5021103" "5162255").PN.	USPAT	2003/09/10 17:29
-	30	(base with (Ge or germanium)) and (collector with (sic or (silicon adj carbide))) and (emitter with (si or silicon))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 17:37
-	37	(base adj (ge or germanium)) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 18:06
-	1	(base adj (SiGe or (silicon adj germanium))) and (emitter adj (sige or (silicon adj germanium))) and (collector adj (SiC or (silicon adj carbide)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 18:08
-	22	(base with (SiGe or (silicon adj germanium))) and (emitter with (sige or (silicon adj germanium))) and (collector with (SiC or (silicon adj carbide)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 18:22
-	1969	(257/77,197,198).CCLS.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 18:35
-	661	((257/77,197,198).CCLS.) and (SiC or (Silicon adj carbide))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 18:36

-	65	((257/77,197,198).CCLS.) and ((SiC or (Silicon adj carbide)) with collector)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/11 18:36
-	4	((("5557118") or ("5441911") or ("6049098") or ("5378921")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/13 11:32
-	7	("2524033" or "2569347" or "2918396" or "4945394" or "4985742" or "5610411" or "6329675").pn.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/13 11:33
-	37	(base with (Ge or germanium)) and (collector with (SiC or (silicon adj carbide))) and (emitter with (Si or silicon))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/07 10:21
-	47	(base with (SiGe) or (Silicon adj germanium)) and (collector with (SiC or (silicon adj carbide))) and (emitter with (SiGe) or (silicon adj germanium))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/07 10:22
-	139	collector with (SiC or (silicon adj carbide) or (carburized adj silicon))	USPAT	2004/10/30 15:00
-	105	(collector with (SiC or (silicon adj carbide) or (carburized adj silicon))) and transistor	USPAT	2004/10/30 15:00
-	96	((collector with (SiC or (silicon adj carbide) or (carburized adj silicon))) and transistor) and (@ad<20011121 or @rlad<20011121)	USPAT	2004/10/30 16:41
-	7	("4945394" "5318915" "5539217" "5726463" "5798277" "5814859" "6143593").PN.	USPAT	2004/10/30 15:59
-	1	((collector with (SiC or (silicon adj carbide) or (carburized adj silicon))) and transistor) and (@ad<20011121 or @rlad<20011121)) and ((wafer adj bonding) or (wafer adj bonded))	USPAT	2004/10/30 16:42
-	0	base with emitter with ((wafer adj bonding) or (wafer adj bonded))	USPAT	2004/10/30 16:44
-	3	base same emitter same ((wafer adj bonding) or (wafer adj bonded))	USPAT	2004/10/30 16:44